

HMW60N105UF7

N-Channel MOS UF7 Power MOSFET

600 V, 31.5 A, 105 mΩ

Description

The 600V MOS UF7 series has ultra-fast body diode performance using E7 technology. MOS UF7 is Power Master Semiconductor's advanced fast recovery Super Junction MOSFET family by utilizing charge balance technology for excellent body diode performance, low on-resistance and reduced gate charge. It combines the benefits of a fast switching performance with ease of usage and robustness. Additionally, we offer low reverse recovery time (trr) and reverse recovery charge (Qrr) for the bridge structure topology, especially for resonant converters (LLC, PSFB, etc.).

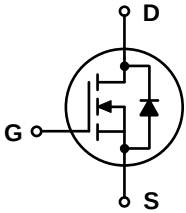
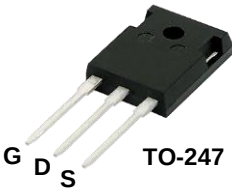
Applications

- Soft Switching Topologies
- Telecom and Sever Power Supplies
- EV Charger and Industrial Power Supplies

Features

$BV_{DSS} @ T_{J,max}$	I_D	$R_{DS(on),max}$	$Q_{g,typ}$
650 V	31.5 A	105 mΩ	53 nC

- Reduced Switching & Conduction Losses
- Fast Recovery Body-Diode
- Lower Gate Resistance
- 100% Avalanche Tested
- Pb-free and RoHS Compliant



Absolute Maximum Ratings ($T_C = 25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter		Value	Unit
V_{DSS}	Drain to Source Voltage		600	V
V_{GSS}	Gate to Source Voltage		± 30	V
I_D	Drain Current	Continuous ($T_C = 25^{\circ}\text{C}$)	31.5	A
		Continuous ($T_C = 100^{\circ}\text{C}$)	19.9	
I_{DM}	Drain Current	Pulsed (Note1)	94.5	A
E_{AS}	Single Pulsed Avalanche Energy (Note2)		187	mJ
I_{AS}	Avalanche Current (Note2)		5.4	A
E_{AR}	Repetitive Avalanche Energy (Note1)		2.6	mJ
dv/dt	MOSFET dv/dt		100	V/ns
	Peak Diode Recovery dv/dt (Note3)		50	
P_D	Power Dissipation	($T_C = 25^{\circ}\text{C}$)	260	W
		Derate Above 25°C	2.08	W/ $^{\circ}\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to 150	$^{\circ}\text{C}$
T_L	Maximum Lead Temperature for Soldering, 1/8" from Case for 10 Seconds		260	$^{\circ}\text{C}$

Thermal Characteristics

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.48	$^{\circ}\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	

Package Marking and Ordering Information

Part Number	Top Marking	Package	Packing Method	Quantity
HMW60N105UF7	HMW60N105UF7	TO-247	Tube	30 units

Electrical Characteristics (T_C = 25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
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Off Characteristics

BV _{DSS}	Drain to Source Breakdown Voltage	V _{GS} = 0 V, I _D = 1 mA	600			V
		V _{GS} = 0 V, I _D = 1 mA, T _J = 150°C	650			
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 600 V, V _{GS} = 0 V			10	μA
		V _{DS} = 480 V, V _{GS} = 0 V, T _J = 125°C		20		
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ±30 V, V _{DS} = 0 V			±100	nA

On Characteristics

V _{GS(th)}	Gate Threshold Voltage	V _{GS} = V _{DS} , I _D = 2.1 mA	3.0		5.0	V
R _{DS(on)}	Static Drain to Source On Resistance	V _{GS} = 10 V, I _D = 15.3 A		89	105	mΩ

Dynamic Characteristics

C _{iss}	Input Capacitance	V _{DS} = 400 V, V _{GS} = 0V, f = 250 kHz		2176		pF
C _{oss}	Output Capacitance			61		pF
C _{o(tr)}	Time Related Output Capacitance	V _{DS} = 0 V to 400 V, V _{GS} = 0 V		629		pF
C _{o(er)}	Energy Related Output Capacitance			96.3		pF
Q _{g(tot)}	Total Gate Charge at 10 V	V _{DS} = 400 V, I _D = 15.3 A, V _{GS} = 10 V		53		nC
Q _{gs}	Gate to Source Charge			13.2		nC
Q _{gd}	Gate to Drain “Miller” Charge			27		nC
R _G	Gate Resistance	f = 1 MHz		1		Ω

Switching Characteristics

t _{d(on)}	Turn-On Delay Time	V _{DS} = 400 V, I _D = 15.3 A, V _{GS} = 10 V, R _G = 10 Ω See Figure 13		21		ns
t _r	Turn-On Rise Time			13		ns
t _{d(off)}	Turn-Off Delay Time			74		ns
t _f	Turn-Off Fall Time			9		ns

Source-Drain Diode Characteristics

I _S	Maximum Continuous Diode Forward Current			31.5	A
I _{SM}	Maximum Pulsed Diode Forward Current			94.5	A
V _{SD}	Diode Forward Voltage	V _{GS} = 0 V, I _{SD} = 15.3 A		1.2	V
t _{rr}	Reverse Recovery Time	V _{DD} = 400 V, I _{SD} = 15.3 A, di _F /dt = 100 A/μs		114	ns
Q _{rr}	Reverse Recovery Charge			0.66	μC

※Notes:

- 1. Repetitive rating: pulse-width limited by maximum junction temperature.
- 2. I_{AS} = 5.4 A, R_G = 25 Ω, starting T_J = 25°C.
- 3. I_{SD} ≤ 15.3 A, di/dt ≤ 100 A/μs, V_{DD} ≤ 400 V, starting T_J = 25°C.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

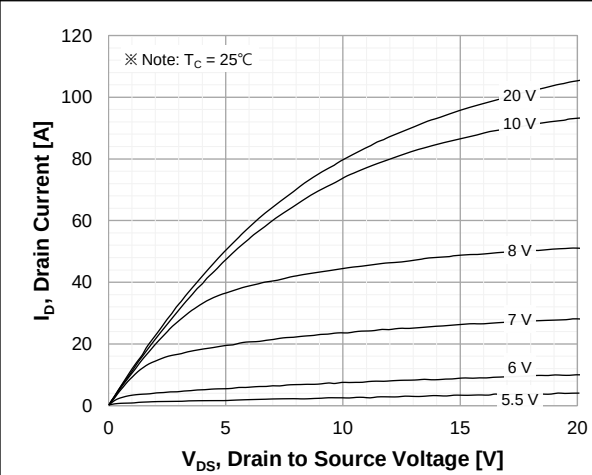


Figure 2. Transfer Characteristics

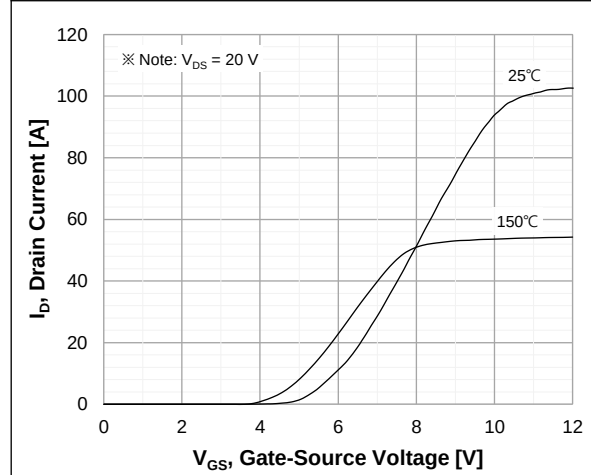


Figure 3. On-Resistance Characteristics vs. Drain Current and Gate Voltage

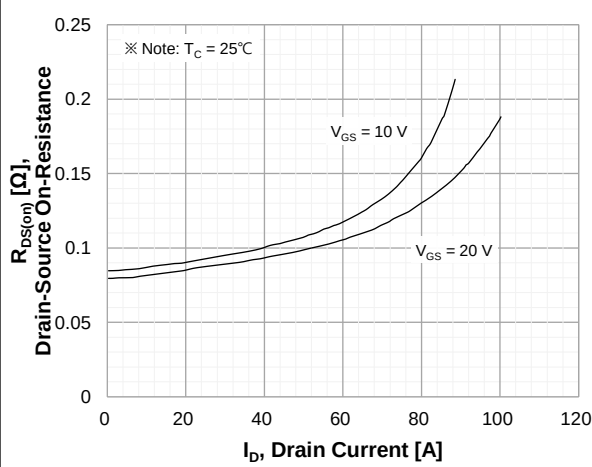


Figure 4. Diode Forward Voltage Characteristics vs. Source-Drain Current and Temperature

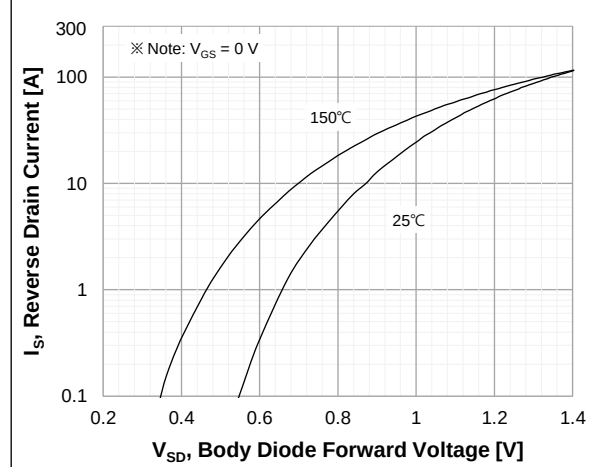


Figure 5. Capacitance Characteristics

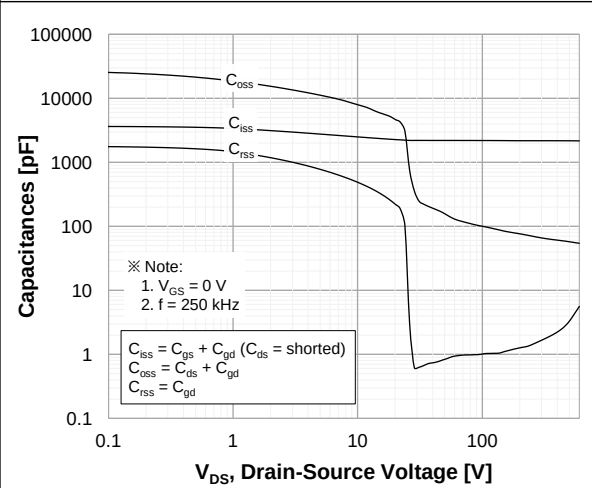
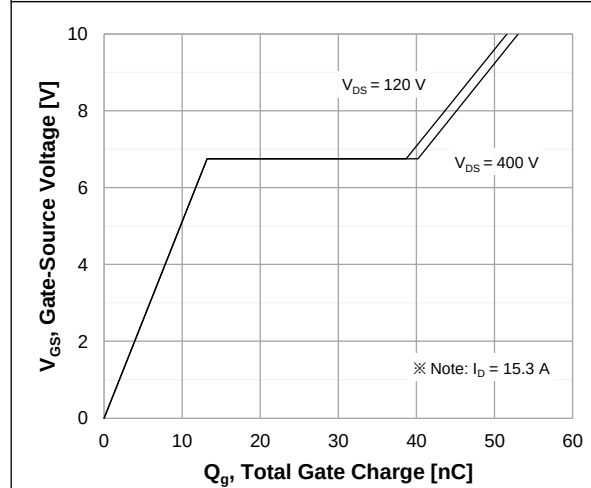


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics

Figure 7. Breakdown Voltage Characteristics vs. Temperature

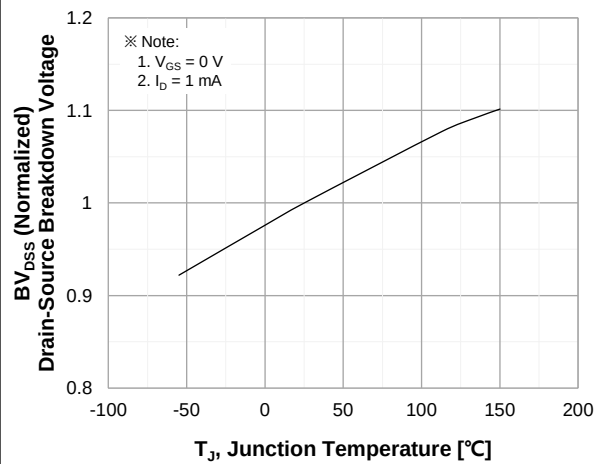


Figure 8. On-Resistance Characteristics vs. Temperature

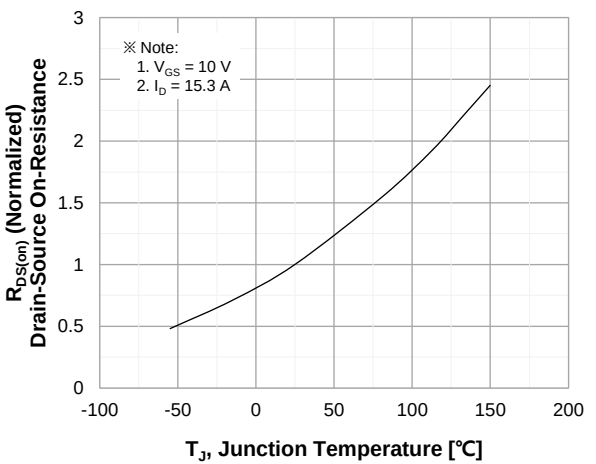


Figure 9. Maximum Safe Operating Area

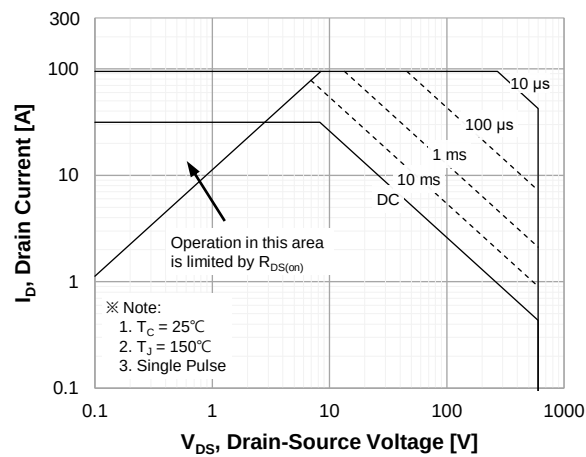


Figure 10. Maximum Drain Current vs. Case Temperature

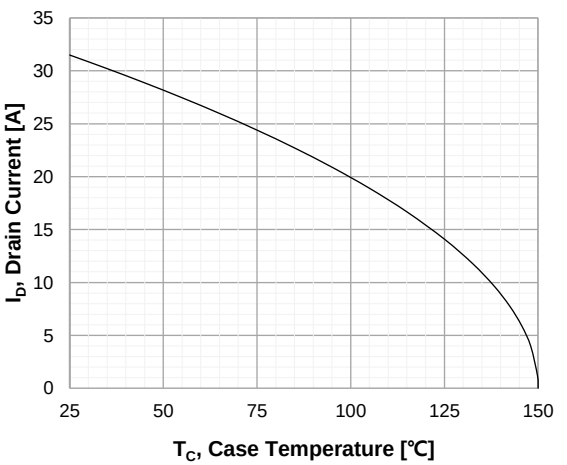


Figure 11. E_{oss} vs. Drain to Source Voltage

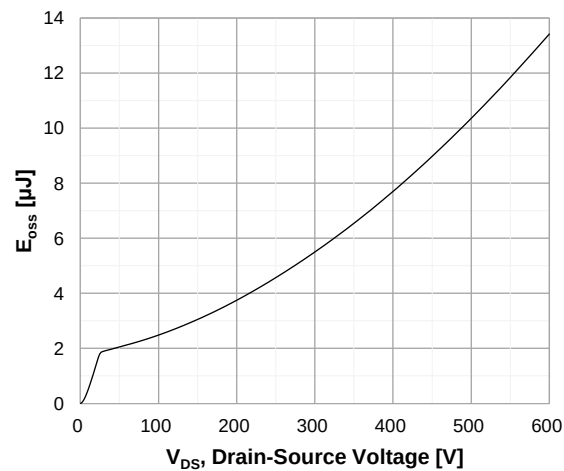
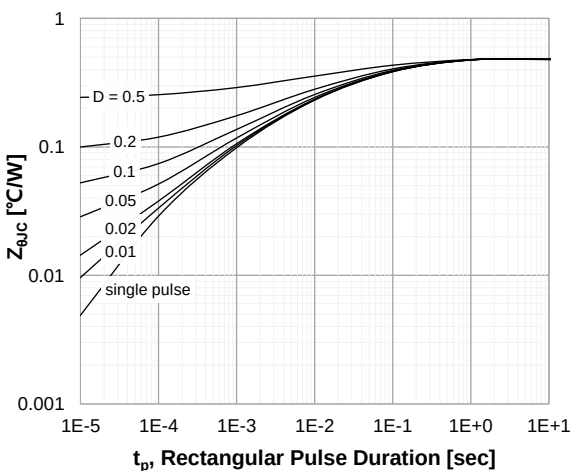


Figure 12. Transient Thermal Response Curve



Test Circuits

Figure 13. Inductive Load Switching Test Circuit and Waveforms

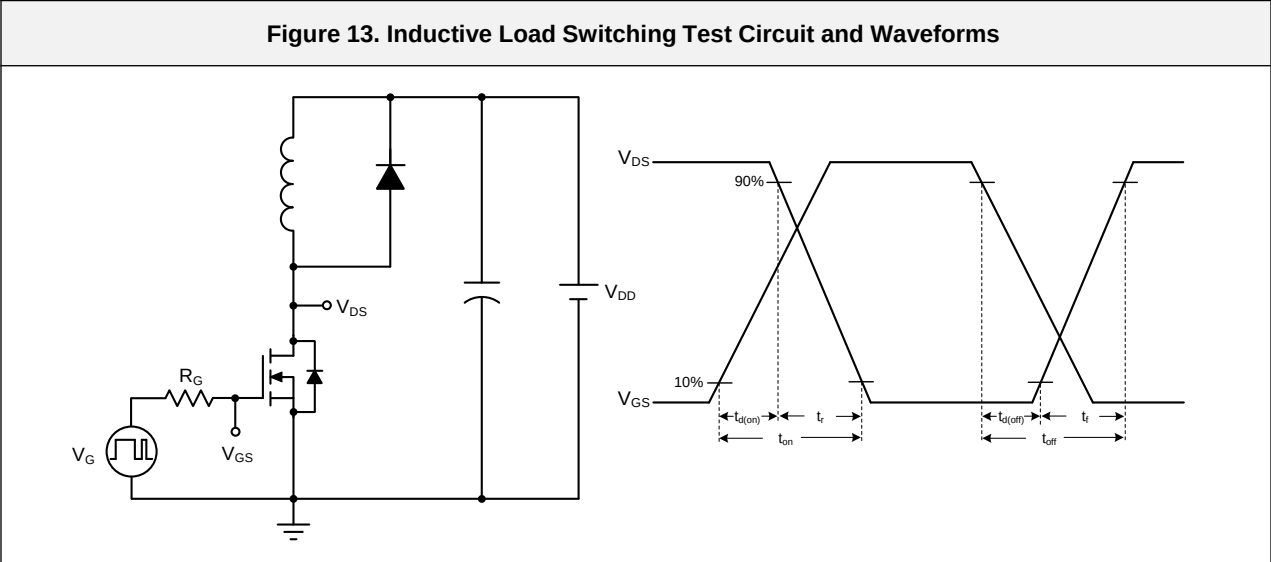


Figure 14. Unclamped Inductive Switching Test Circuit and Waveforms

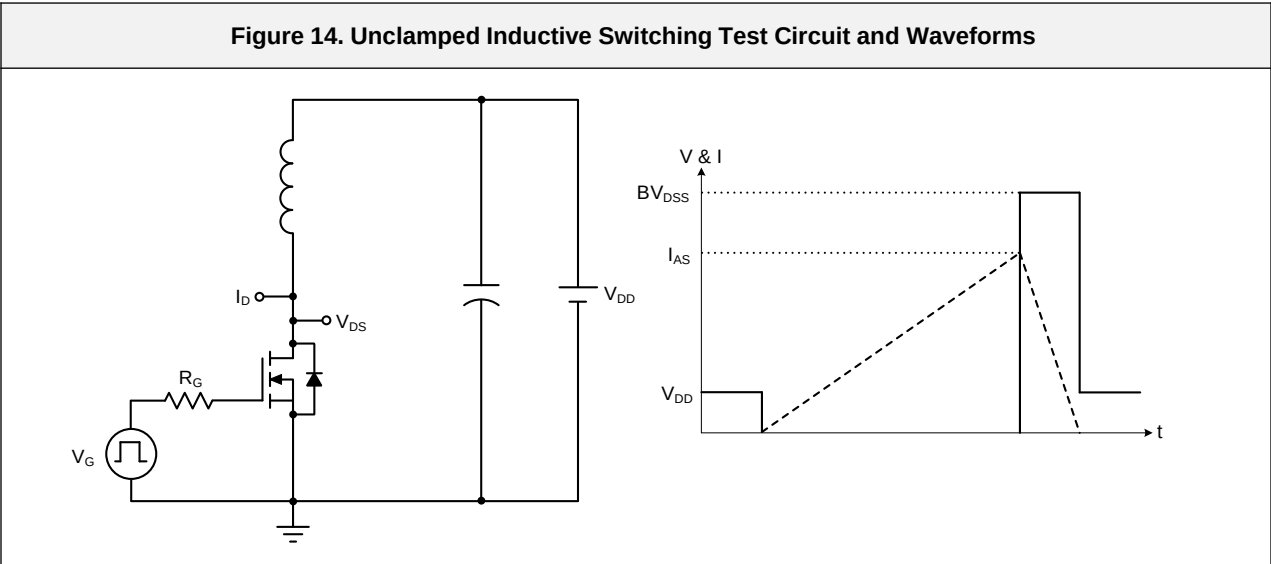
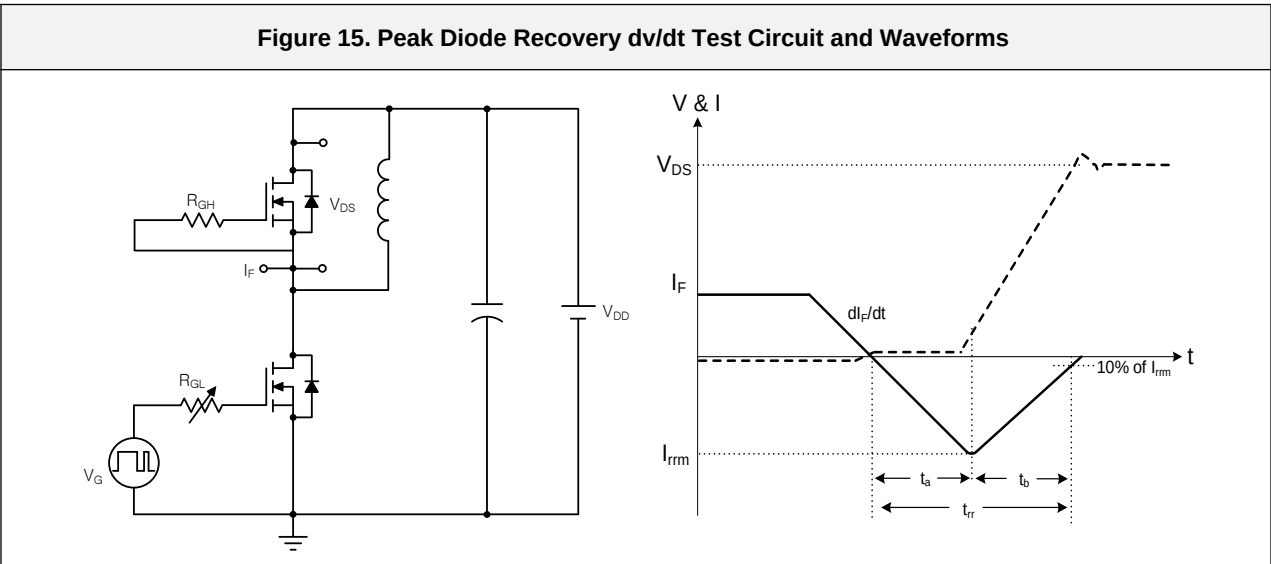
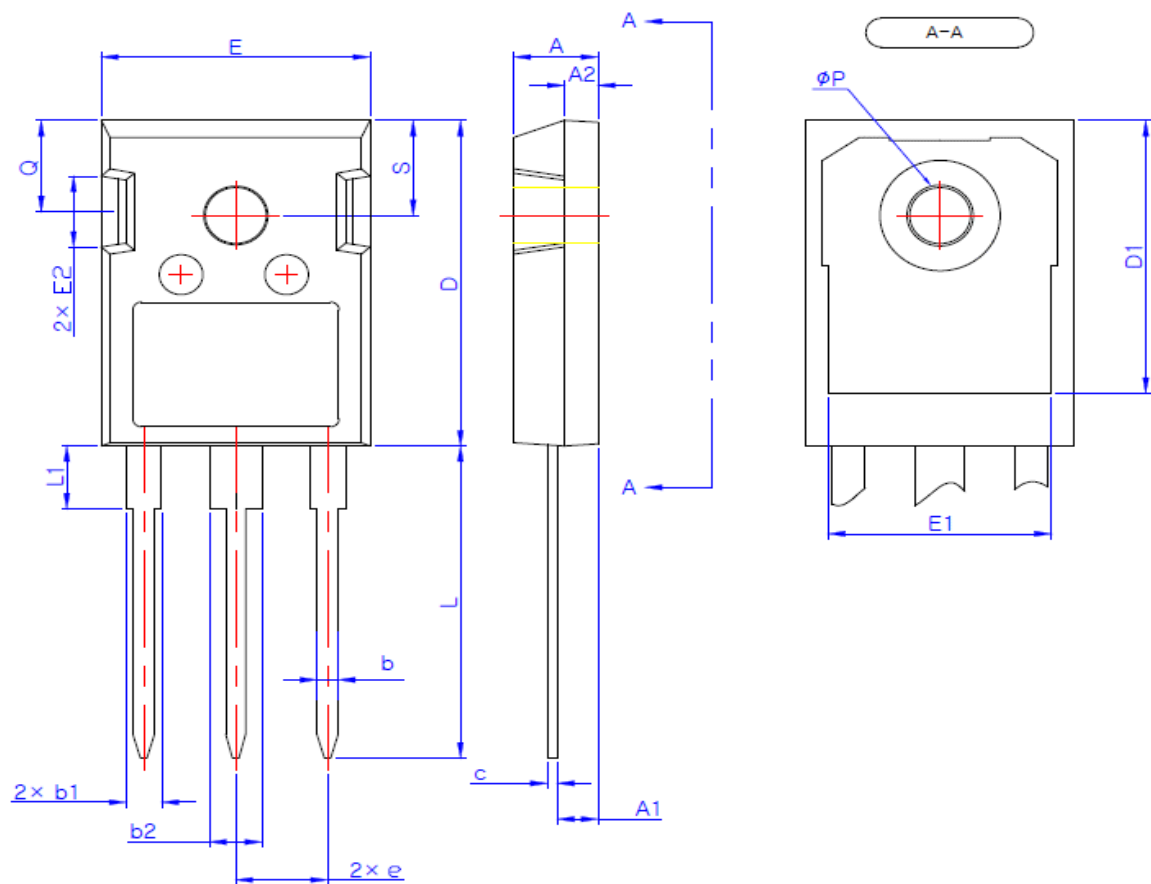


Figure 15. Peak Diode Recovery dv/dt Test Circuit and Waveforms



Package Outlines

TO-247



SYMBOL	MIN	NOM	MAX
A	4.80	5.00	5.20
A1	2.29	2.42	2.54
A2	1.90	2.00	2.10
b	1.10	1.20	1.30
b1	1.91	2.06	2.20
b2	2.92	3.06	3.20
c	0.50	0.60	0.70
D	20.80	21.07	21.34
D1	17.43	17.63	17.83
E	15.75	15.94	16.13
E1	13.06	13.26	13.46
E2	4.32	4.58	4.83
e	5.45 BSC		
L	19.85	20.05	20.25
L1	4.05	4.27	4.49
ΦP	3.55	3.60	3.65
Q	5.59	5.89	6.19
S	6.15 BSC		

* Dimensions in millimeters